### TOSHIBA ALLOY-FREE LIGHT TRIGGER THYRISTOR

# **SL3500LX21**

#### HIGH POWER CONTROL APPLICATIONS

Repetitive Peak Off-State Voltage :  $V_{DRM}$  = 8000V

Repetitive Peak Reverse Voltage

 $: I_{T(AV)} = 3500A$ Average On-State Current

: PLT: 8mW (Max.) Light Trigger Power

Turn-Off Time :  $t_0 = 400 \mu s$  (Max.)

Critical Rate of Rise of On-State Current

:  $di/dt = 200A/\mu s$ 

Critical Rate of Rise of Off-State Voltage

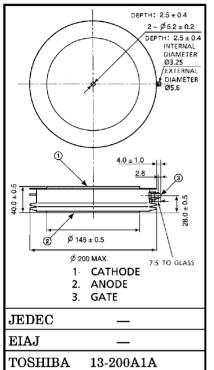
:  $dv/dt = 2300V/\mu s$ 

Flat Package

## MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and Repetitive Peak Reverse Voltage	${ m v_{DRM}} \ { m v_{RRM}}$	8000	V	
Non-Repetitive Peak Reverse Voltage (Non-Repetitive $\leq 5$ ms, $T_j = 0 \sim 115$ °C)	V <sub>RSM</sub>	8800	V	
R.M.S On-State Current	IT (RMS)	5498	Α	
Average On-State Current	I <sub>T (AV)</sub>	3500	Α	
Peak One Cycle Surge On-State Current (Non-Repetitive)	ITSM	60000 (50Hz) 65000 (60Hz)	Α	
I <sup>2</sup> t Limit Value	$ m I^2 t$	$180 \times 10^{5}$	$\mathbf{A}^2\mathbf{s}$	
Critical Rate of Rise of On-State Current (Note)	di / dt	200	A/μs	
Junction Temperature	$T_{j}$	-40~120	°C	
Storage Temperature Range	$T_{ m stg}$	-40~120	°C	
Mounting Force	_	98.0±9.8	kN	

Unit in mm



Weight: 6500g

Note:  $V_D=1/2$  Rated,  $T_i=120$ °C

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# **ELECTRICAL CHARACTERISTICS**

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Repetitive Peak Off-State Current and Repetitive Peak Reverse Current	IDRM I <sub>RRM</sub>	$V_{ m DRM} = V_{ m RRM} = { m Rated},$ $T_{ m j} = 120 { m ^{\circ}C}$				700	mA
Peak On-State Voltage	$ m V_{TM}$	$I_{TM} = 2800A, T_j = 25^{\circ}C$			_	2.7	V
Light Trigger Power	D	$V_D = 12V, R_L = 6\Omega$ $T_j =$	= <b>-4</b> 0°C		_	_	<b>XX</b>
	$\mathrm{P_{LT}}$	$ VD^{-12}V, RL^{-622} $ $ T_j=$	=25°C			8	mW
Delay Time	$^{ m t_d}$	$V_D=1/2$ Rated, $T_j=25$ °C,	,			4	μs
Gate Turn-On Time	$ m t_{gt}$	$P_L = 24 \text{mW}$			_	10	$\mu$ s
Turn-Off Time	$\mathbf{t}_{\mathbf{q}}$	$I_{T}$ =2500A, $V_{R}$ \geq 500V, $dv/dt$ =25V/ $\mu$ s, $T_{j}$ =90°C, $V_{DRM}$ =1/2 Rated				400	μs
Holding Current	$I_{\mathrm{H}}$	$T_j=25$ °C, $R_L=6\Omega$			_	_	mA
Critical Rate of Rise of Off-State Voltage	dv / dt	V <sub>DRM</sub> =1/2 Rated, T <sub>j</sub> =90°C, Gate Open, Exponential Rise		2300			V/μs
Thermal Resistance (Junction to Case)	R <sub>th (j-f)</sub>	DC		_	_	0.0035	°C/W